

### **60V N-Channel Enhancement Mode MOSFET**

Voltage

60 V

Current

410mA

### **Features**

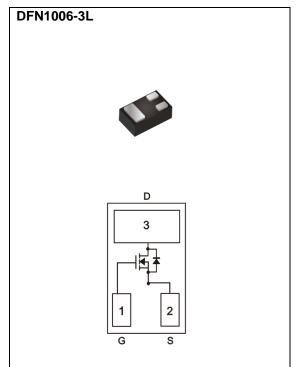
- RDS(ON), VGS@10V, ID@600mA<3 $\Omega$
- RDS(ON), VGS@4.5V, ID@200mA< $4\Omega$
- Advanced Trench Process Technology
- Specially Designed for Switch Load
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### **Mechanical Data**

• Case: DFN1006-3L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0007 grams



# **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	60	· V	
Gate-Source Voltage		V <sub>GS</sub>	±30		
Continuous Drain Current(Note 4)		I <sub>D</sub>	410	mA	
Pulsed Drain Current(Note 1)		I <sub>DM</sub>	1200		
Power Dissipation	T <sub>A</sub> =25°C		900	mW	
	Derate above 25°C	PD	7.2	mW/°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C	
Thermal Resistance - Junction to Ambient, t<10s <sup>(Note 5)</sup>		$R_{ heta JA}$	139	°C/W	



### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

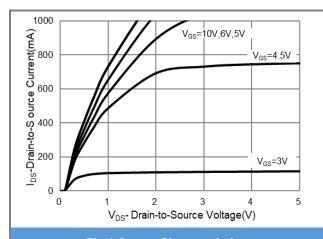
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub> V <sub>GS</sub> =0V, I <sub>D</sub> =250uA		60	-	-		
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.8	2.5	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =600mA	-	1.3	3	Ω	
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =200mA	-	1.7	4		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0V	-	-	±100	nA	
Dynamic <sup>(Note 6)</sup>							
Total Gate Charge	Qg	V <sub>DS</sub> =15V, I <sub>D</sub> =600mA,	-	0.82	-	nC	
Gate-Source Charge	Qgs		-	0.53	-		
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =4.5V	-	0.22	-		
Input Capacitance	Ciss	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	34	-	pF	
Output Capacitance	Coss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,	-	11	-		
Reverse Transfer Capacitance	Crss	f=1MHz	-	3	-		
Turn-On Delay Time	td <sub>(on)</sub>		-	2.7	-		
Turn-On Rise Time	tr	V <sub>DD</sub> =10V, I <sub>D</sub> =600mA,	-	21	-	ns	
Turn-Off Delay Time	td(off)	$V_{GS}=10V$ , $R_{G}=6\Omega^{(Note 1,2)}$	-	3.8	-		
Turn-Off Fall Time	tf	KG=Ω(Σ(1,000-1,2)	-	18	-		
Drain-Source Diode			•				
Diode Forward Current	Is		-	-	300	mA	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =300mA, V <sub>GS</sub> =0V	-	0.9	1.5	V	

#### NOTES:

- 1. Pulse width < 300us, Duty cycle < 2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial  $T_J$ =25°C.
- 4. The maximum current rating is package limited.
- 5. R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.



#### **TYPICAL CHARACTERISTIC CURVES**



**Fig.1 Output Characteristics** 

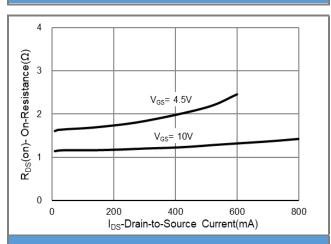
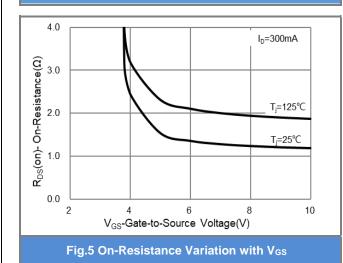
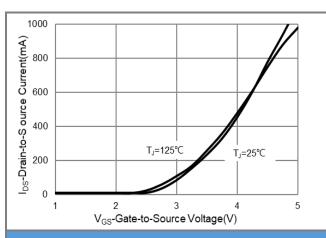


Fig.3 On-Resistance vs. Drain Current





**Fig.2 Transfer Characteristics** 

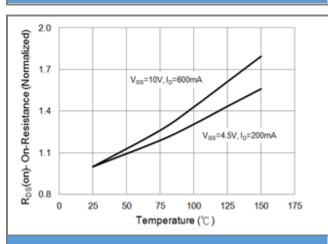


Fig.4 On-Resistance vs. Junction temperature

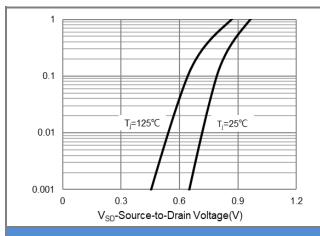


Fig.6 Source-Drain Diode Forward Voltage



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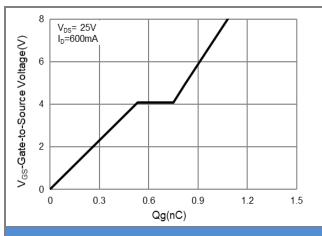
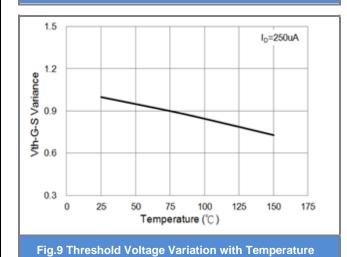


Fig.7 Gate-Charge Characteristics



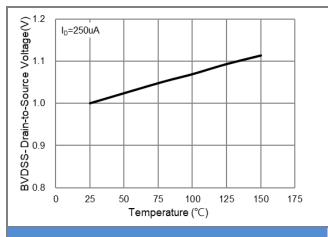


Fig.8 Breakdown Voltage Variation vs. Temperature

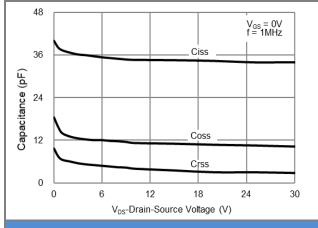


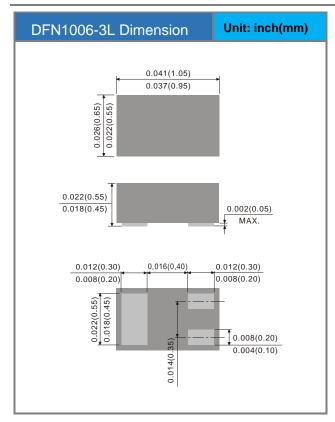
Fig.10 Capacitance vs. Drain-Source Voltage

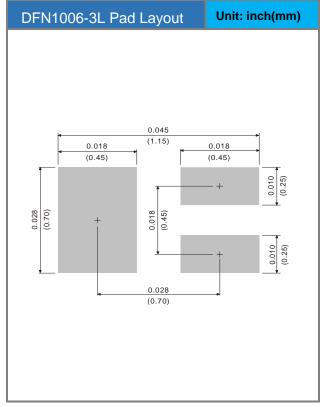


### **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking	
PJQ1972	DFN1006-3L	10K pcs / 7" reel	U	

## **Packaging Information & Mounting Pad Layout**







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